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FIG.10A PRIOR ART

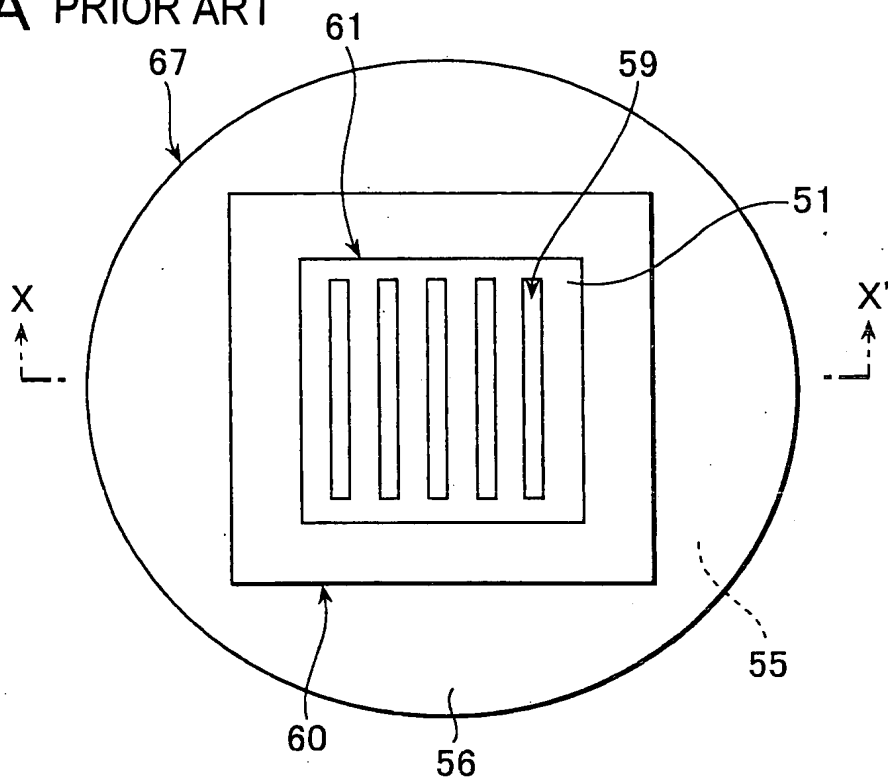
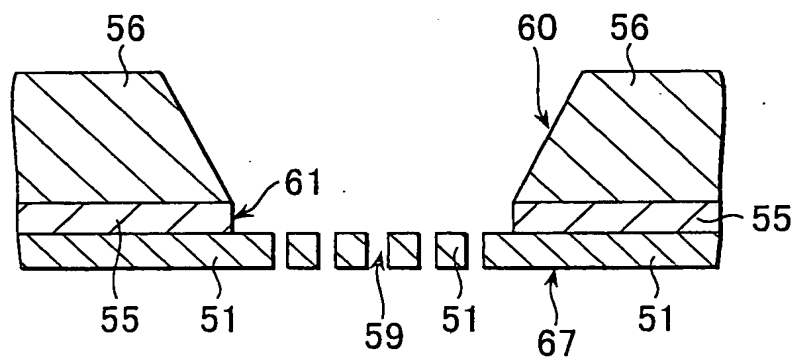


FIG.10B PRIOR ART

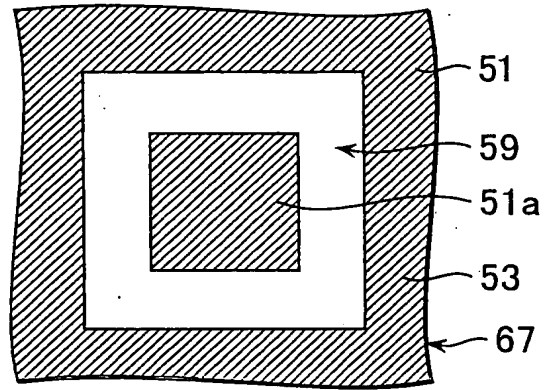
X-X' CROSS SECTION



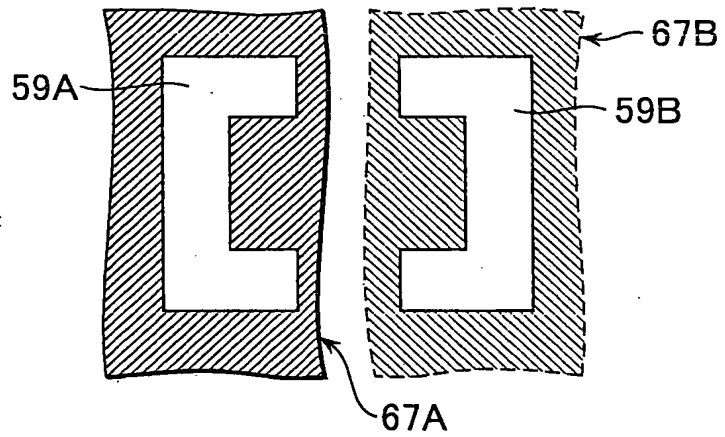
This diagram shows a cross-sectional view of a semiconductor device during an exposure step. The device consists of several layers: a top layer 56, a layer 55, a layer 51, and a substrate 57. A photoresist layer 60 is applied to the top surface of layer 56. The photoresist is being exposed by a series of vertical beams 71. The exposed areas of the photoresist are labeled 61. The unexposed areas are labeled 67. The word "EXPOSURE" is written above the beams. The substrate 57 is shown with a pattern of alternating layers 54 and 55. A layer 58 is also indicated at the bottom. A label 59 points to the interface between the photoresist and the underlying layers.

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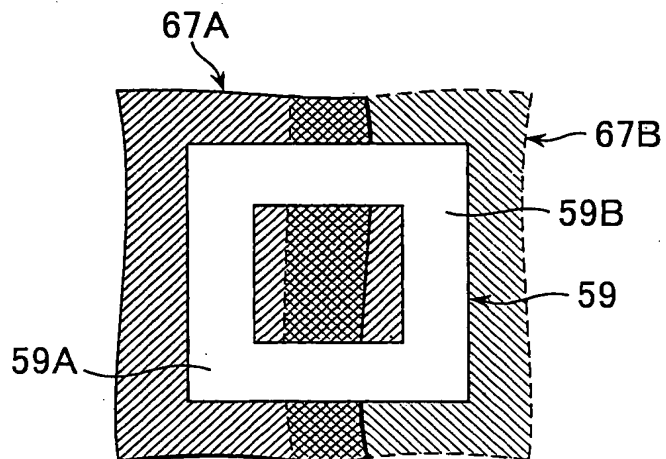
**FIG.12A**  
PRIOR ART



**FIG.12B**  
PRIOR ART

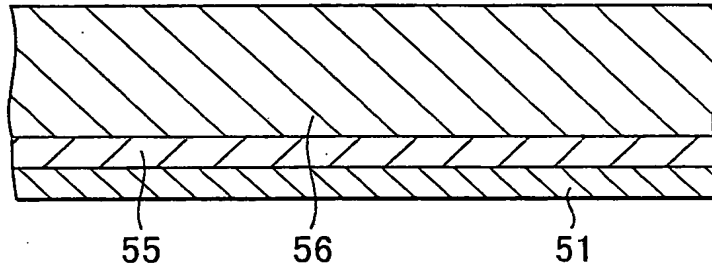


**FIG.12C**  
PRIOR ART

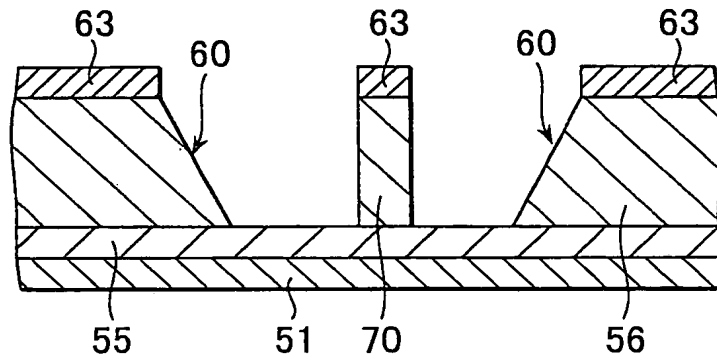


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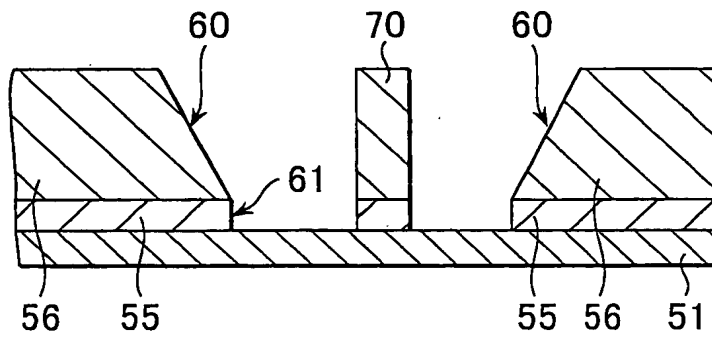
**FIG.13A**  
PRIOR ART



**FIG.13B**  
PRIOR ART

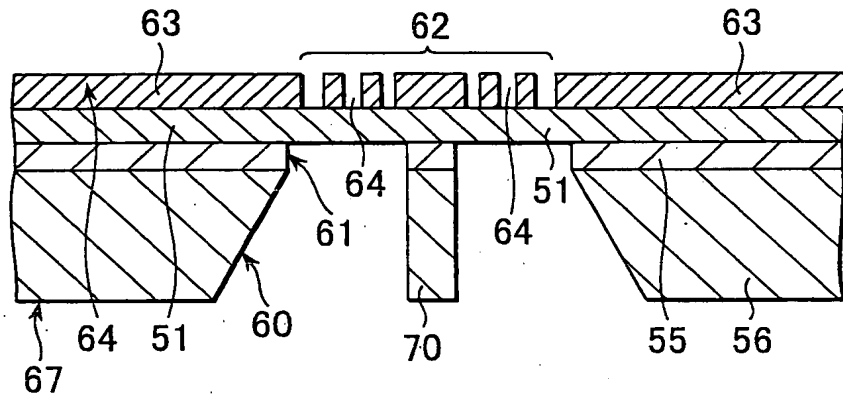


**FIG.13C**  
PRIOR ART

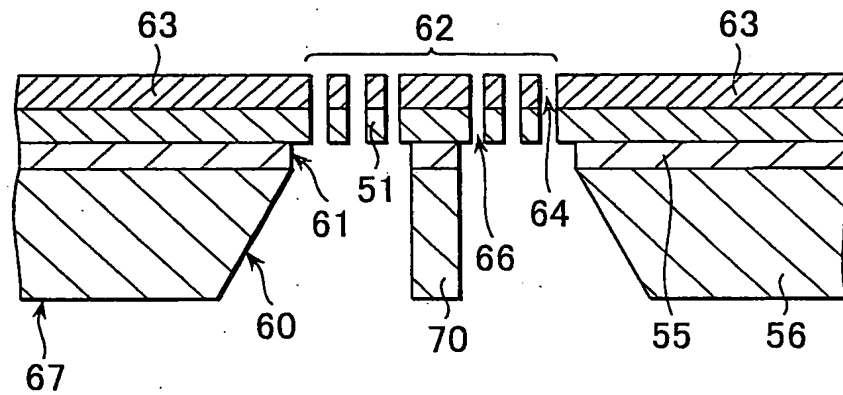


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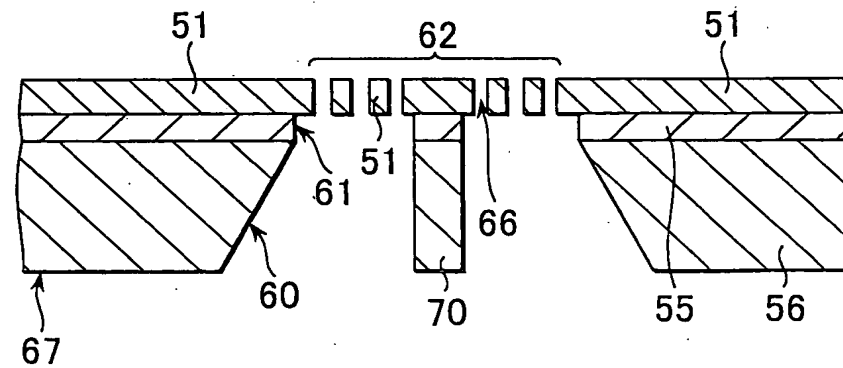
**FIG.14A**  
PRIOR ART



**FIG.14B**  
PRIOR ART



**FIG.14C**  
PRIOR ART



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FIG.15 PRIOR ART

